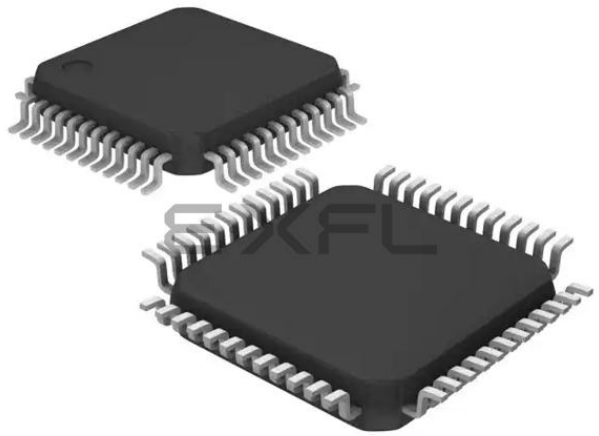
Renesas Electronics America Inc - R5F104GHDFB#30 Datasheet



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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104ghdfb-30

○ ROM, RAM capacities

Flash ROM	Data flash	RAM	RL78/G14			
			30 pins	32 pins	36 pins	40 pins
192 KB	8 KB	20 KB	—	—	—	R5F104EH
128 KB	8 KB	16 KB	R5F104AG	R5F104BG	R5F104CG	R5F104EG
96 KB	8 KB	12 KB	R5F104AF	R5F104BF	R5F104CF	R5F104EF
64 KB	4 KB	5.5 KB Note	R5F104AE	R5F104BE	R5F104CE	R5F104EE
48 KB	4 KB	5.5 KB Note	R5F104AD	R5F104BD	R5F104CD	R5F104ED
32 KB	4 KB	4 KB	R5F104AC	R5F104BC	R5F104CC	R5F104EC
16 KB	4 KB	2.5 KB	R5F104AA	R5F104BA	R5F104CA	R5F104EA

Flash ROM	Data flash	RAM	RL78/G14			
			44 pins	48 pins	52 pins	64 pins
512 KB	8 KB	48 KB Note	—	R5F104GL	—	R5F104LL
384 KB	8 KB	32 KB	—	R5F104GK	—	R5F104LK
256 KB	8 KB	24 KB Note	R5F104FJ	R5F104GJ	R5F104JJ	R5F104LJ
192 KB	8 KB	20 KB	R5F104FH	R5F104GH	R5F104JH	R5F104LH
128 KB	8 KB	16 KB	R5F104FG	R5F104GG	R5F104JG	R5F104LG
96 KB	8 KB	12 KB	R5F104FF	R5F104GF	R5F104JF	R5F104LF
64 KB	4 KB	5.5 KB Note	R5F104FE	R5F104GE	R5F104JE	R5F104LE
48 KB	4 KB	5.5 KB Note	R5F104FD	R5F104GD	R5F104JD	R5F104LD
32 KB	4 KB	4 KB	R5F104FC	R5F104GC	R5F104JC	R5F104LC
16 KB	4 KB	2.5 KB	R5F104FA	R5F104GA	—	—

Flash ROM	Data flash	RAM	RL78/G14	
			80 pins	100 pins
512 KB	8 KB	48 KB Note	R5F104ML	R5F104PL
384 KB	8 KB	32 KB	R5F104MK	R5F104PK
256 KB	8 KB	24 KB Note	R5F104MJ	R5F104PJ
192 KB	8 KB	20 KB	R5F104MH	R5F104PH
128 KB	8 KB	16 KB	R5F104MG	R5F104PG
96 KB	8 KB	12 KB	R5F104MF	R5F104PF

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F104xD (x = A to C, E to G, J, L): Start address FE900H

R5F104xE (x = A to C, E to G, J, L): Start address FE900H

R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H

R5F104xL (x = G, L, M, P): Start address F3F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

(2/2)

Item		30-pin R5F104Ax (x = F, G)	32-pin R5F104Bx (x = F, G)	36-pin R5F104Cx (x = F, G)	40-pin R5F104Ex (x = F to H)
Clock output/buzzer output		2	2	2	2
		[30-pin, 32-pin, 36-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) [40-pin products] • 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)			
8/10-bit resolution A/D converter		8 channels	8 channels	8 channels	9 channels
D/A converter		1 channel	2 channels		
Comparator		2 channels			
Serial interface		[30-pin, 32-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel [36-pin, 40-pin products] • CSI: 1 channel/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 1 channel • CSI: 1 channel/UART: 1 channel/simplified I^2C: 1 channel • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels			
	I^2C bus	1 channel	1 channel	1 channel	1 channel
Data transfer controller (DTC)		30 sources			31 sources
Event link controller (ELC)		Event input: 21 Event trigger output: 8	Event input: 21, Event trigger output: 9		Event input: 22 Event trigger output: 9
Vectored interrupt sources	Internal	24	24	24	24
	External	6	6	6	7
Key interrupt		—	—	—	4
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access			
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)			
Voltage detector		1.63 V to 4.06 V (14 stages)			
On-chip debug function		Provided			
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = –40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = –40 to +105°C)			
Operating ambient temperature		T_A = –40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)			

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution not is issued by emulation with the in-circuit emulator or on-chip debug emulator.

2.3 DC Characteristics

2.3.1 Pin characteristics

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high Note 1	I_{OH1}	Per pin for P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	1.6 V ≤ EV_{DD0} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P40 to P47, P102, P120, P130, P140 to P145 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-55.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-10.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			-5.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147 (When duty ≤ 70% Note 3)	4.0 V ≤ EV_{DD0} ≤ 5.5 V			-80.0	mA
			2.7 V ≤ EV_{DD0} < 4.0 V			-19.0	mA
			1.8 V ≤ EV_{DD0} < 2.7 V			-10.0	mA
			1.6 V ≤ EV_{DD0} < 1.8 V			-5.0	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EV_{DD0} ≤ 5.5 V			-135.0 Note 4	mA
	I_{OH2}	Per pin for P20 to P27, P150 to P156	1.6 V ≤ V_{DD} ≤ 5.5 V			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V_{DD} ≤ 5.5 V			-1.5	mA

Note 1. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.

Note 2. Do not exceed the total current value.

Note 3. Specification under conditions where the duty factor ≤ 70%.
The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (I_{OH} × 0.7)/(n × 0.01)

<Example> Where n = 80% and I_{OH} = -10.0 mA
Total output current of pins = (-10.0 × 0.7)/(80 × 0.01) ≈ -8.7 mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor.
A current higher than the absolute maximum rating must not flow into one pin.

Note 4. -100 mA for industrial applications (R5F104xxDxx, R5F104xxGxx).

Caution **P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 do not output high level in N-ch open-drain mode.**

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.9		mA
						V_{DD} = 3.0 V		2.9		
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.5		
						V_{DD} = 3.0 V		2.5		
			HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		6.0	11.2	mA
						V_{DD} = 3.0 V		6.0	11.2	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.5	10.6	
						V_{DD} = 3.0 V		5.5	10.6	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.7	8.6	
						V_{DD} = 3.0 V		4.7	8.6	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.4	8.2	
						V_{DD} = 3.0 V		4.4	8.2	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		3.3	5.9	
						V_{DD} = 3.0 V		3.3	5.9	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.5	2.5	mA
						V_{DD} = 2.0 V		1.5	2.5	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.5	2.1	mA
						V_{DD} = 2.0 V		1.5	2.1	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		3.7	6.8	mA
						Resonator connection		3.9	7.0	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.7	6.8	
						Resonator connection		3.9	7.0	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.4	2.4	mA
						Resonator connection		1.4	2.5	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.4	2.4	
						Resonator connection		1.4	2.5	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		5.2		µA
						Resonator connection		5.2		
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		5.3	7.7	
						Resonator connection		5.3	7.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		5.5	10.6	
						Resonator connection		5.5	10.6	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		5.9	13.2	
						Resonator connection		6.0	13.2	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		6.8	17.5	
						Resonator connection		6.9	17.5	

(**Notes** and **Remarks** are listed on the next page.)

Note 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.

Note 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.

Note 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.

Note 8. Current flowing during programming of the data flash.

Note 9. Current flowing during self-programming.

Note 10. For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/G14 User's Manual.

Note 11. Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DAC} when the D/A converter operates in an operation mode or the HALT mode.

Note 12. Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.

Note 13. A comparator and D/A converter are provided in products with 96 KB or more code flash memory.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

Note 4. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 3** above to calculate the maximum transfer rate under conditions of the customer.

Note 5. Use it with $EV_{DD0} \geq V_b$.

Note 6. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 7. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 6** above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

(T_A = -40 to +85°C, 2.7 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 2/f_{CLK}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ	200		1150		1150		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ	300		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		t_{KCY1}/2 - 120		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 7		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 10		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
SIp setup time (to SCKp↑) Note 1	t_{SIK1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		58		479		479		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		121		479		479		ns
SIp hold time (from SCKp↑) Note 1	t_{KSI1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ		10		10		10		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ		10		10		10		ns
Delay time from SCKp↓ to SOp output Note 1	t_{KSO1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 20 pF, R_b = 1.4 kΩ			60		60		60	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 20 pF, R_b = 2.7 kΩ			130		130		130	ns

(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

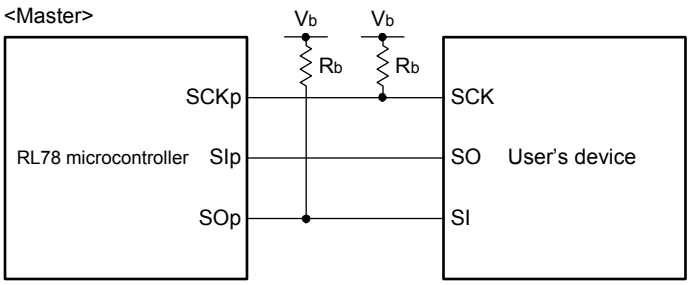
Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	t_{KCY1}	$t_{KCY1} \geq 4/f_{CLK}$	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ	300		1150		1150		ns
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ	500		1150		1150		ns
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ	1150		1150		1150		ns
SCKp high-level width	t_{KH1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		t_{KCY1}/2 - 75		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		t_{KCY1}/2 - 170		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		t_{KCY1}/2 - 458		ns
SCKp low-level width	t_{KL1}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ		t_{KCY1}/2 - 12		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ		t_{KCY1}/2 - 18		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note, C_b = 30 pF, R_b = 5.5 kΩ		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		t_{KCY1}/2 - 50		ns

Note Use it with $EV_{DD0} \geq V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)

CSI mode connection diagram (during communication at different potential



Remark 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

Remark 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)

Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

Remark 4. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

2.5.2 Serial interface IICA

(1) I^2C standard mode

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	f_{SCL}	Standard mode: f_{CLK} ≥ 1 MHz	2.7 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.8 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EV_{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV_{DD0} ≤ 5.5 V	—		0	100	0	100	kHz
Setup time of restart condition	$t_{SU: STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.7		4.7		µs
Hold time Note 1	$t_{HD: STA}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.0		4.0		µs
Hold time when SCLA0 = “L”	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.7		4.7		4.7		µs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.7		4.7		µs
Hold time when SCLA0 = “H”	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.8 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.7 V ≤ EV_{DD0} ≤ 5.5 V		4.0		4.0		4.0		µs
		1.6 V ≤ EV_{DD0} ≤ 5.5 V		—		4.0		4.0		µs

(**Notes**, **Caution**, and **Remark** are listed on the next page.)

2.6.6 LVD circuit characteristics

(1) Reset Mode and Interrupt Mode

(T_A = -40 to +85°C, $V_{PDR} \leq V_{DD} \leq$ 5.5 V, V_{SS} = 0 V)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Voltage detection threshold	Supply voltage level	V_{LVD0}	Rising edge	3.98	4.06	4.14	V
			Falling edge	3.90	3.98	4.06	V
		V_{LVD1}	Rising edge	3.68	3.75	3.82	V
			Falling edge	3.60	3.67	3.74	V
		V_{LVD2}	Rising edge	3.07	3.13	3.19	V
			Falling edge	3.00	3.06	3.12	V
		V_{LVD3}	Rising edge	2.96	3.02	3.08	V
			Falling edge	2.90	2.96	3.02	V
		V_{LVD4}	Rising edge	2.86	2.92	2.97	V
			Falling edge	2.80	2.86	2.91	V
		V_{LVD5}	Rising edge	2.76	2.81	2.87	V
			Falling edge	2.70	2.75	2.81	V
		V_{LVD6}	Rising edge	2.66	2.71	2.76	V
			Falling edge	2.60	2.65	2.70	V
		V_{LVD7}	Rising edge	2.56	2.61	2.66	V
			Falling edge	2.50	2.55	2.60	V
		V_{LVD8}	Rising edge	2.45	2.50	2.55	V
			Falling edge	2.40	2.45	2.50	V
		V_{LVD9}	Rising edge	2.05	2.09	2.13	V
			Falling edge	2.00	2.04	2.08	V
		V_{LVD10}	Rising edge	1.94	1.98	2.02	V
			Falling edge	1.90	1.94	1.98	V
		V_{LVD11}	Rising edge	1.84	1.88	1.91	V
			Falling edge	1.80	1.84	1.87	V
		V_{LVD12}	Rising edge	1.74	1.77	1.81	V
			Falling edge	1.70	1.73	1.77	V
		V_{LVD13}	Rising edge	1.64	1.67	1.70	V
			Falling edge	1.60	1.63	1.66	V
Minimum pulse width		t_{LW}		300			µs
Detection delay time						300	µs

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications T_A = -40 to +105°C

R5F104xxGxx

Caution 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.

Caution 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.

Caution 3. The pins mounted depend on the product. Refer to 2.1 Port Functions to 2.2.1 Functions for each product in the RL78/G14 User's Manual.

Caution 4. Please contact Renesas Electronics sales office for derating of operation under T_A = +85 to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G14 is used in the range of T_A = -40 to +85°C, see **2. ELECTRICAL SPECIFICATIONS (T_A = -40 to +85°C)**.

3.4 AC Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	µs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} ≤ 2.7 V			1.0		16.0	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} ≤ 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			µs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10 Note			ns
Timer RJ input cycle	f_C	TRJIO		2.7 V ≤ EV_{DD0} ≤ 5.5 V	100			ns
				2.4 V ≤ EV_{DD0} < 2.7 V	300			ns
Timer RJ input high-level width, low-level width	t_{TJIH}, t_{TJIL}	TRJIO		2.7 V ≤ EV_{DD0} ≤ 5.5 V	40			ns
				2.4 V ≤ EV_{DD0} < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}
2.4 V ≤ EV_{DD0} < 2.7 V: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time Note 1	t_{KCY2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V	24 MHz < f_{MCK}	28/f_{MCK}		ns
			20 MHz < f_{MCK} ≤ 24 MHz	24/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 20 MHz	20/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V	24 MHz < f_{MCK}	40/f_{MCK}		ns
			20 MHz < f_{MCK} ≤ 24 MHz	32/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	28/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	24/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	16/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	12/f_{MCK}		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V	24 MHz < f_{MCK}	96/f_{MCK}		ns
			20 MHz < f_{MCK} ≤ 24 MHz	72/f_{MCK}		ns
			16 MHz < f_{MCK} ≤ 20 MHz	64/f_{MCK}		ns
			8 MHz < f_{MCK} ≤ 16 MHz	52/f_{MCK}		ns
			4 MHz < f_{MCK} ≤ 8 MHz	32/f_{MCK}		ns
			f_{MCK} ≤ 4 MHz	20/f_{MCK}		ns
SCKp high-/low-level width	t_{KH2}, t_{KL2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		t_{KCY2}/2 - 24		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		t_{KCY2}/2 - 36		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		t_{KCY2}/2 - 100		ns
SIp setup time (to SCKp↑) Note 2	t_{SIK2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		1/f_{MCK} + 40		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		1/f_{MCK} + 40		ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		1/f_{MCK} + 60		ns
SIp hold time (from SCKp↑) Note 3	t_{KSI2}			1/f_{MCK} + 62		ns
Delay time from SCKp↓ to SOp output Note 4	t_{KSO2}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 30 pF, R_b = 1.4 kΩ			2/f_{MCK} + 240	ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 30 pF, R_b = 2.7 kΩ			2/f_{MCK} + 428	ns
		2.4 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V, C_b = 30 pF, R_v = 5.5 kΩ			2/f_{MCK} + 1146	ns

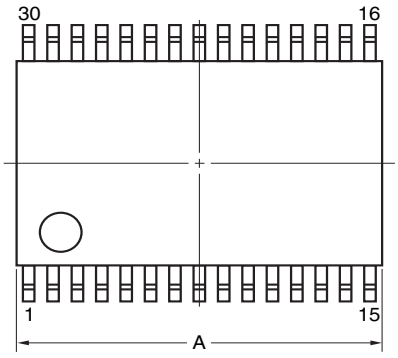
(**Notes**, **Caution**, and **Remarks** are listed on the next page.)

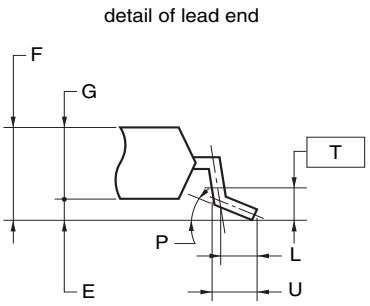
4. PACKAGE DRAWINGS

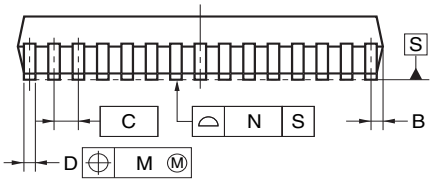
4.1 30-pin products

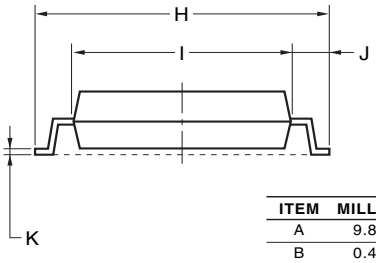
R5F104AAASP, R5F104ACASP, R5F104ADASP, R5F104AEASP, R5F104AFASP, R5F104AGASP
R5F104AADSP, R5F104ACDSP, R5F104ADDSP, R5F104AEDSP, R5F104AFDSP, R5F104AGDSP
R5F104AAGSP, R5F104ACGSP, R5F104ADGSP, R5F104AEGSP, R5F104AFGSP, R5F104AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18









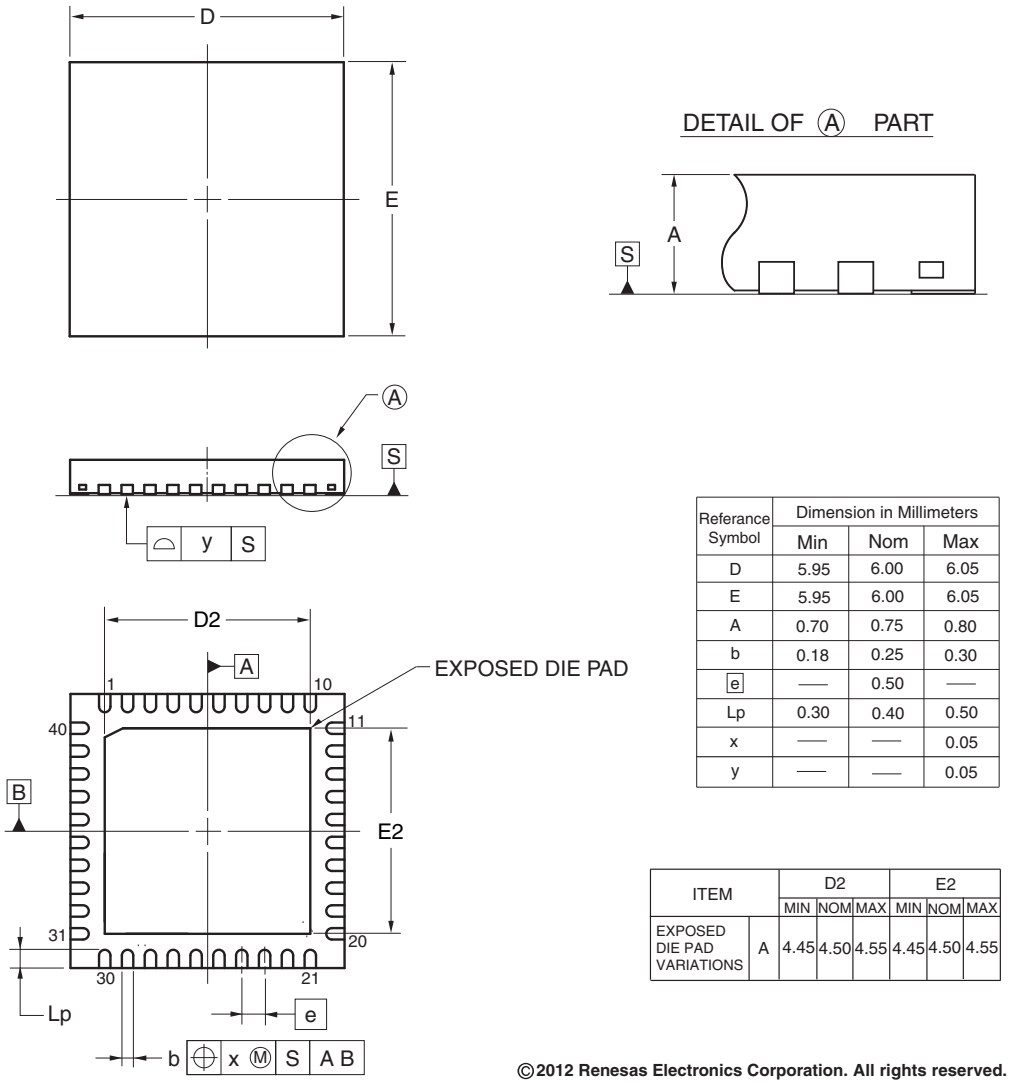
NOTE
Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.15
B	0.45 MAX.
C	0.65 (T.P.)
D	$0.24^{+0.08}_{-0.07}$
E	0.1±0.05
F	1.3±0.1
G	1.2
H	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
P	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
T	0.25
U	0.6±0.15

4.4 40-pin products

R5F104EAANA, R5F104ECANA, R5F104EDANA, R5F104EEANA, R5F104EFANA, R5F104EGANA, R5F104EHANA
R5F104EADNA, R5F104ECDNA, R5F104EDDNA, R5F104EEDNA, R5F104EFDNA, R5F104EGDNA, R5F104EHDNA
R5F104EAGNA, R5F104ECGNA, R5F104EDGNA, R5F104EEGNA, R5F104EFGNA, R5F104EGGNA, R5F104EHGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-4	0.09

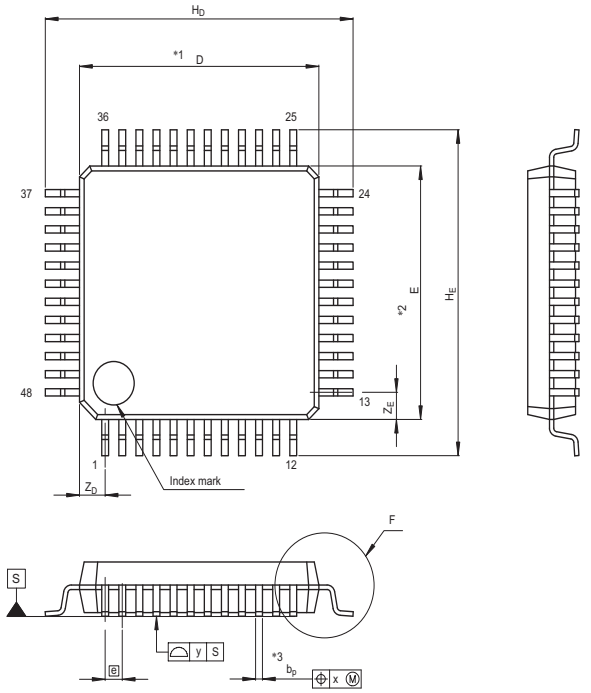


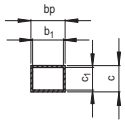
Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	5.95	6.00	6.05
E	5.95	6.00	6.05
A	0.70	0.75	0.80
b	0.18	0.25	0.30
e	—	0.50	—
Lp	0.30	0.40	0.50
x	—	—	0.05
y	—	—	0.05

ITEM		D2			E2		
		MIN	NOM	MAX	MIN	NOM	MAX
EXPOSED DIE PAD VARIATIONS	A	4.45	4.50	4.55	4.45	4.50	4.55

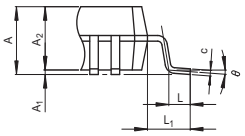
R5F104GKAFB, R5F104GLAFB
R5F104GKGFB, R5F104GLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g





Terminal cross section



Detail F

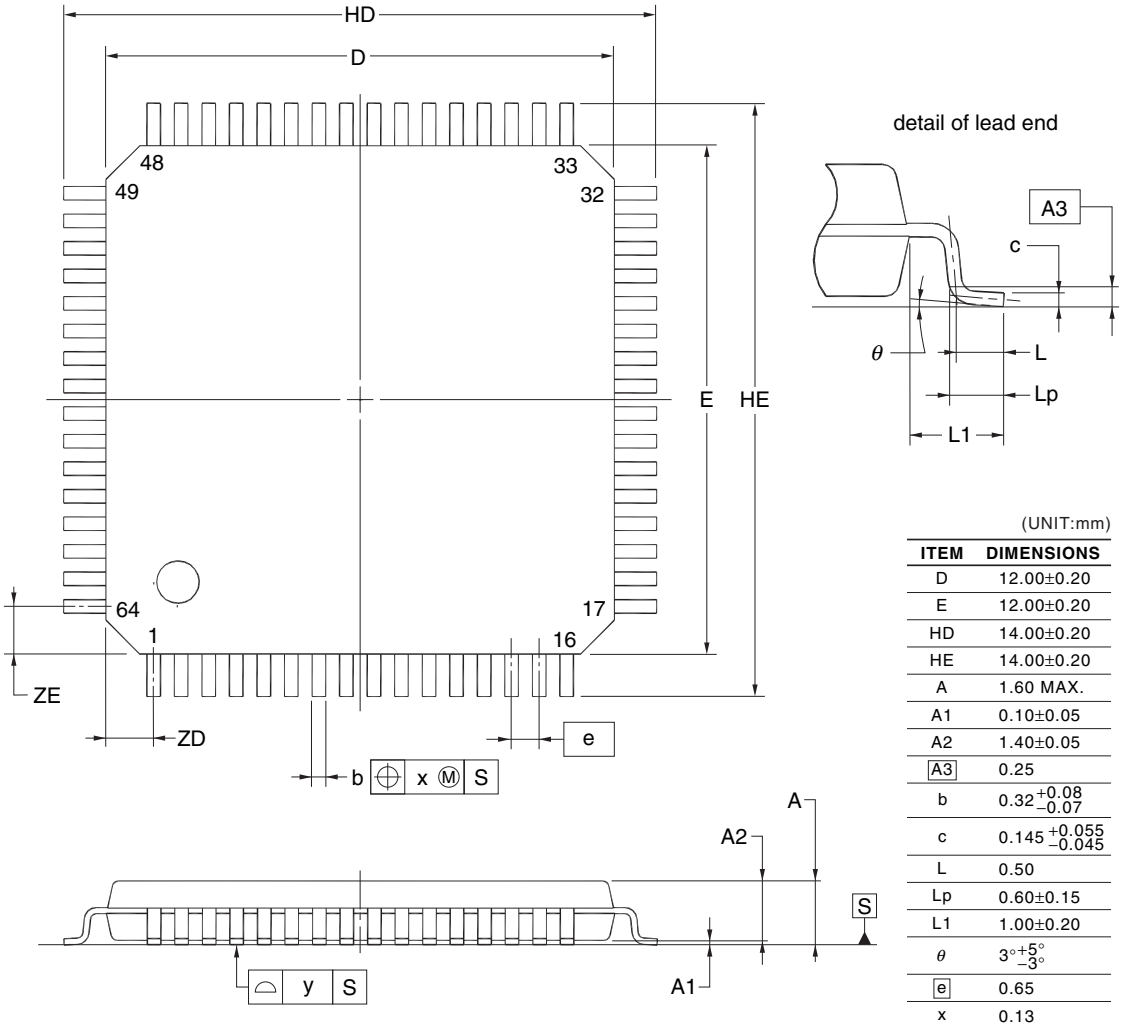
NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

4.8 64-pin products

R5F104LCAFA, R5F104LDAFA, R5F104LEAFA, R5F104LFAFA, R5F104LGAFA, R5F104LHAFA, R5F104LJAFA
R5F104LCDFA, R5F104LDDFA, R5F104LEDFA, R5F104LFDFA, R5F104LGDFA, R5F104LHDFA, R5F104LJDFA
R5F104LCGFA, R5F104LDGFA, R5F104LEGFA, R5F104LFGFA, R5F104LGGFA, R5F104LHGFA, R5F104LJGFA
R5F104LKAFA, R5F104LLAFA
R5F104LKGFA, R5F104LLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



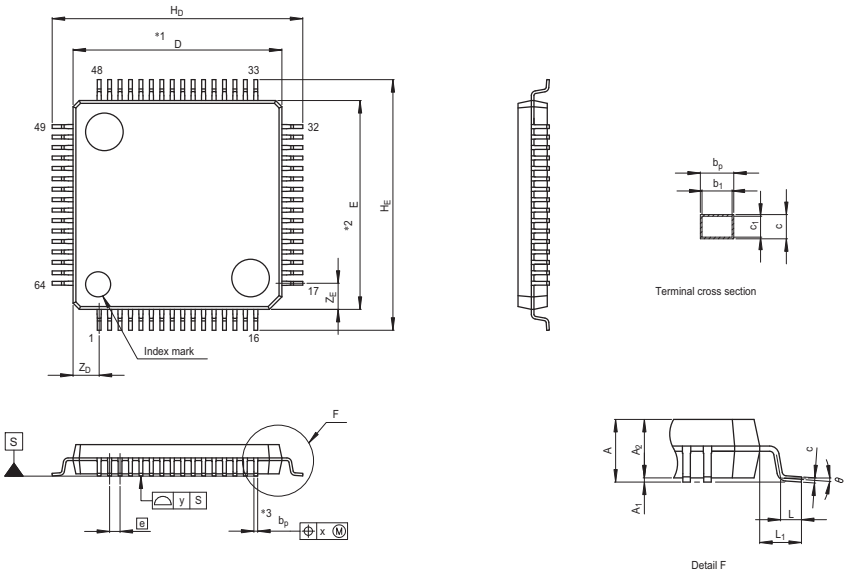
(UNIT:mm)

ITEM	DIMENSIONS
D	12.00±0.20
E	12.00±0.20
HD	14.00±0.20
HE	14.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.65
x	0.13
y	0.10
ZD	1.125
ZE	1.125

NOTE
Each lead centerline is located within 0.13 mm of its true position at maximum material condition.

R5F104LKAFB, R5F104LLAFB
R5F104LKGFB, R5F104LLGFB

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LFQFP64-10x10-0.50	PLQP0064KB-A	64P6Q-A / FP-64K / FP-64KV	0.3g



NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A_2	—	1.4	—
H_D	11.8	12.0	12.2
H_E	11.8	12.0	12.2
A	—	—	1.7
A_1	0.05	0.1	0.15
b_p	0.15	0.20	0.25
b_1	—	0.18	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.08
Z_D	—	1.25	—
Z_E	—	1.25	—
L	0.35	0.5	0.65
L_1	—	1.0	—